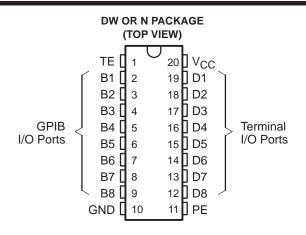
SN75ALS160 OCTAL GENERAL-PURPOSE INTERFACE BUS TRANSCEIVERS

SLLS018E - JUNE 1986 - REVISED JUNE 2004



- 8-Channel Bidirectional Transceivers
- High-Speed Advanced Low-Power Schottky (ALS) Circuitry
- Low Power Dissipation
 ... 46 mW Max Per Channel
- Fast Propagation Times . . . 20 ns Max
- High-Impedance pnp Inputs
- Receiver Hysteresis . . . 650 mV Typ
- Open-Collector Driver Output Option
- No Loading of Bus When Device Is Powered Down (V_{CC} = 0)
- Power-Up/Power-Down Protection (Glitch Free)



description/ordering information

The SN75ALS160 eight-channel general-purpose interface bus transceivers are monolithic, high-speed, advanced low-power Schottky (ALS) devices designed for two-way data communications over single-ended transmission lines. This device is designed to meet the requirements of IEEE Standard 488-1978. The transceivers feature driver outputs that can be operated in either the passive-pullup or 3-state mode. If talk enable (TE) is high, these ports have the characteristics of passive-pullup outputs when pullup enable (PE) is low and of 3-state outputs when PE is high. Taking TE low places these ports in the high-impedance state. The driver outputs are designed to handle loads up to 48 mA of sink current.

An active turn-off feature has been incorporated into the bus-terminating resistors so that the device exhibits a high impedance to the bus when $V_{CC} = 0$. When combined with the SN75ALS161 or SN75ALS162 bus management transceiver, the pair provides the complete 16-wire interface for the IEEE-488 bus.

The SN75ALS160 is characterized for operation from 0°C to 70°C.

ORDERING INFORMATION

TA	PACK	AGE†	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	PDIP (N)	Tube of 20	SN75ALS160N	SN75ALS160N	
0°C to 70°C	SOIC (DW)	Tube of 25	SN75ALS160DW	7541.0400	
		Reel of 2000	SN75ALS160DWR	75ALS160	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design quidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



Function Tables

EACH DRIVER

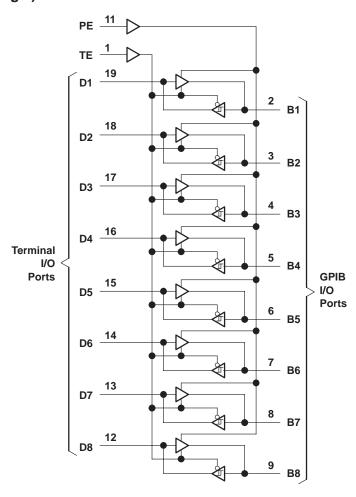
	INPUTS		OUTPUT
D	TE	PE	В
Н	Н	Н	Н
L	Н	X	L
Н	Χ	L	z†
Х	L	X	z†

EACH RECEIVER

	INPUTS	OUTPUT	
В	TE	PE	D
L	L	Х	L
Н	L	X	Н
Х	Н	X	Z

H = high level, L = low level, X = irrelevant, Z = high-impedance state

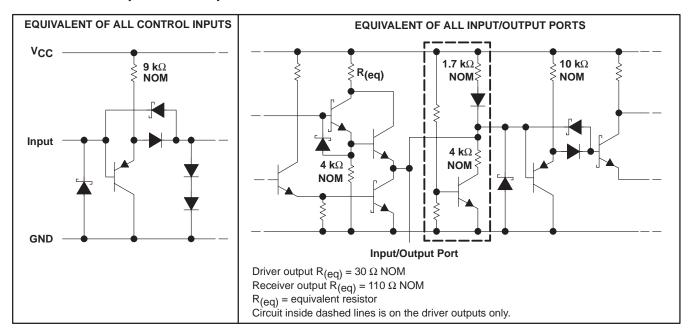
logic diagram (positive logic)





[†]This is the high-impedance state of a normal 3-state output modified by the internal resistors to V_{CC} and GND.

schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{CC} (see Note 1)	7 V
Input voltage, V _I	
Low-level driver output current, I _{OL}	. 100 mA
Package thermal impedance, θ _{JA} (see Notes 2 and 3): DW package	. 58°C/W
N package	. 69°C/W
Operating virtual junction temperature, T _J	150°C
Storage temperature range, T _{stq} –65°C	to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to network ground terminal.
 - 2. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



SN75ALS160 OCTAL GENERAL-PURPOSE INTERFACE BUS TRANSCEIVERS

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recommended operating conditions

			MIN	NOM	MAX	UNIT
VCC	Supply voltage		4.75	5	5.25	V
V_{IH}	High-level input voltage		2			V
V_{IL}	Low-level input voltage				0.8	V
		Bus ports with pullups active			- 5.2	mA
ІОН	High-level output current	Terminal ports			- 800	μΑ
		Bus ports			48	
lOL	Low-level output current	Terminal ports			16	mA
TA	Operating free-air temperature		0		70	°C

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER		TE	EST CONDITIONS†		MIN	TYP‡	MAX	UNIT
VIK	Input clamp voltage		$I_{I} = -18 \text{ mA},$	V _{CC} = MIN			- 0.8	- 1.5	V
V _{hys}	Hysteresis voltage (V _{IT+} – V _{IT} _)	Bus				0.4	0.65		V
., 8	High-level output	Terminal	$I_{OH} = -800 \mu A$,	TE at 0.8 V,	V _{CC} = MIN	2.7	3.5		
V _{OH} §	OH ⁹ voltage		$I_{OH} = -5.2 \text{ mA},$	PE and TE at 2 V,	$V_{CC} = MIN$	2.5	3.3		V
V	Low-level output	Terminal	I _{OL} = 16 mA,	TE at 0.8 V,	$V_{CC} = MIN$		0.3	0.5	V
VOL	voltage	Bus	I _{OL} = 48 mA,	TE at 2 V,	$V_{CC} = MIN$		0.35	0.5	V
lį	Input current at maximum input voltage	Terminal	V _I = 5.5 V,	V _{CC} = MAX			0.2	100	μΑ
lіН	High-level input current	Terminal, PE, or TE	V _I = 2.7 V,	V _{CC} = MAX			0.1	20	μΑ
IIL	Low-level input current	Terminal, PE, or TE	V _I = 0.5 V,	V _{CC} = MAX			-10	-100	μΑ
			$I_{I(bus)} = 0$			2.5	3	3.7	V
V _{I/O(bus)}	Voltage at bus port		$I_{I(bus)} = -12 \text{ mA}$			-1.5	V		
				$V_{I(bus)} = -1.5 \text{ V to}$	$V_{I(bus)} = -1.5 \text{ V to } 0.4 \text{ V}$				
				$V_{I(bus)} = 0.4 \text{ V to } 3$	2.5 V	0		- 3.2	
II/O(bus)	Current into bus	Power on		$V_{I(bus)} = 2.5 V to 3$	3.7 V			2.5 - 3.2	mA
., - ()	port			$V_{I(bus)} = 3.7 \text{ V to }$	5 V	0		2.5	
				$V_{I(bus)} = 5 V to 5.5$	5 V	0.7		2.5	
		Power off	$V_{CC} = 0$	$V_{I(bus)} = 0 \text{ to } 2.5 \text{ V}$	V			40	μΑ
1	Short-circuit output	Terminal	$V_{CC} = MAX$			- 15	- 35	- 75	mA
los	current	Bus	$V_{CC} = MAX$			- 25	- 50	- 125	MA
loo	Supply current		No load,	Terminal outputs lo		42	65	mA	
Icc	Supply current		V _{CC} = MAX	Bus outputs low ar	nd enabled		52	80	IIIA
C _{I/O(bus)}	Bus-port capacitance	!	$V_{CC} = 0$ to 5 V,	$V_{I/O} = 0 \text{ to } 2 \text{ V},$	f = 1 MHz		30		pF

[†] For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.



 $[\]ddagger$ All typical values are at V_{CC} = 5 V, T_A = 25°C. § V_{OH} applies to 3-state outputs only.

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switching characteristics at V_{CC} = 4.75 V, 5 V, and 5.25 V, T_A = 25°C (unless otherwise noted)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	түр†	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	Tomologi	Divis	See Figure 1,		10	17	
tPHL	Propagation delay time, high- to low-level output	Terminal	Bus	$C_L = 50 pF$		10	14	ns
tPLH	Propagation delay time, low- to high-level output	Due	Tamasinal	See Figure 2,		8	15	
tPHL	Propagation delay time, high- to low-level output	Bus	Terminal	$C_L = 50 \text{ pF}$		8	15	ns
tPZH	Output enable time to high level					24	30	
^t PHZ			Bus	See Figure 3, C _L = 50 pF		9	14	ns
tPZL						16	28	
tPLZ	Output disable time from low level					12	19	
tPZH	Output enable time to high level					24	36	
tPHZ	Output disable time from high level		To make a t	See Figure 4,		10	18	ns
tPZL	Output enable time to low level	TE	Terminal	$C_L = 50 pF$		15	26	
tPLZ	Output disable time from low level					15	24	
t _{en}	Output pullup enable time	DE	Divis	See Figure 5,		16	24	
tdis	Output pullup disable time	PE	Bus	$C_L = 50 pF$		9	16	ns

[†] All typical values are at $V_{CC} = 5 \text{ V}$.

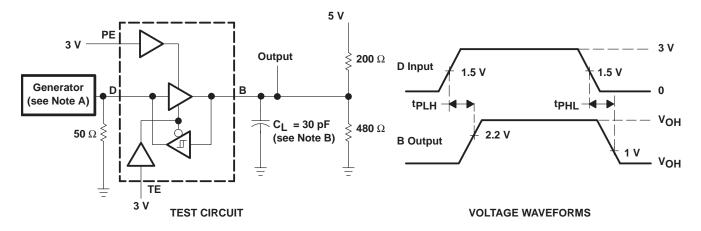
switching characteristics over recommended range of operating free-air temperature, $V_{CC} = 5 \text{ V}$

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	ТҮР‡	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	T	D	$C_L = 30 \text{ pF},$		7	20	
tPHL	Propagation delay time, high- to low-level output	Terminal	Bus	See Figure 1		8	20	ns
tPLH	Propagation delay time, low- to high-level output	Divis	Tomorbook	C _L = 30 pF,		7	14	
tPHL	Propagation delay time, high- to low-level output	Bus	Terminal	See Figure 2		9	14	ns
tPZH	Output enable time to high level			C _L = 15 pF,		19	30	
tPHZ	Output disable time from high level		D.v.o			5	12	
tPZL	Output enable time to low level	TE	Bus	See Figure 3		16	35	ns
tPLZ	Output disable time from low level					9	20	
^t PZH	Output enable time to high level					13	30	
tPHZ	Output disable time from high level			$C_L = 15 pF$,		12	20	
tPZL	Output enable time to low level	TE	Terminal	See Figure 4		12	20	ns
tPLZ	Output disable time from low level					11	20	
t _{en}	Output pullup enable time	DE	Due	C _L = 15 pF,		11	22	
t _{dis}	Output pullup disable time	PE	Bus	See Figure 5		6	12	ns

[‡] Typical values are at $T_A = 25$ °C.

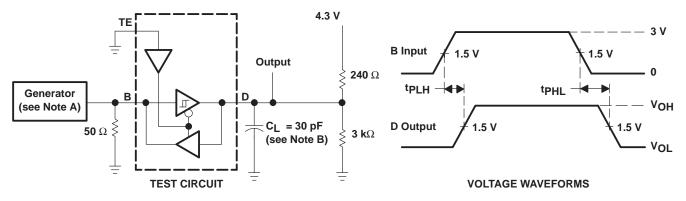


PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, $t_f \leq$ 6 ns, $t_f \leq$ 8 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, t_f
 - B. C_L includes probe and jig capacitance.

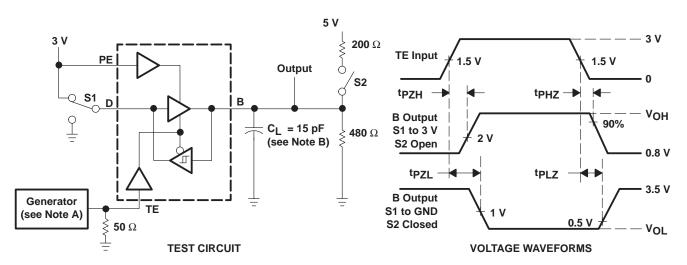
Figure 1. Terminal-to-Bus Test Circuit and Voltage Waveforms



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, $t_f \leq$ 6 ns, $t_f \leq$ 8 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, t_f
 - B. C_L includes probe and jig capacitance.

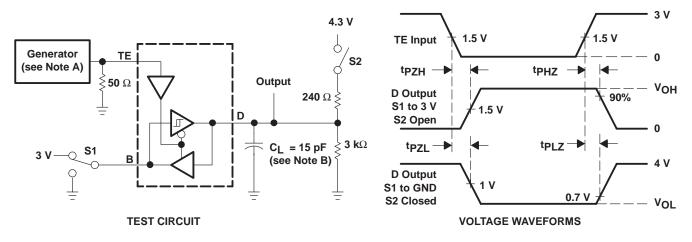
Figure 2. Bus-to-Terminal Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, $t_f \leq$ 6 ns, $t_f \leq$ 8 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, t_f
 - B. CL includes probe and jig capacitance.

Figure 3. TE-to-Bus Test Circuit and Voltage Waveforms

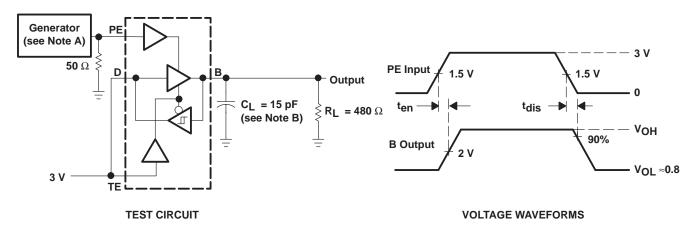


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, $t_f \leq$ 6 ns, $t_f \leq$ 8 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, t_f
 - B. C_L includes probe and jig capacitance.

Figure 4. TE-to-Terminal Test Circuit and Voltage Waveforms

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PARAMETER MEASUREMENT INFORMATION



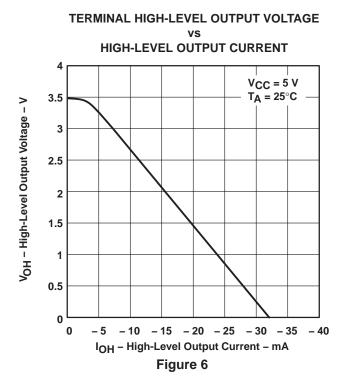
NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 1 MHz, 50% duty cycle, $t_f \leq$ 6 ns, $t_f \leq$ 8 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, t_f

B. C_L includes probe and jig capacitance.

Figure 5. PE-to-Bus Test Circuit and Voltage Waveforms



TYPICAL CHARACTERISTICS



TERMINAL LOW-LEVEL OUTPUT VOLTAGE LOW-LEVEL OUTPUT CURRENT 0.6 V_{CC} = 5 V $T_A = 25^{\circ}C$ V_{OL} - Low-Level Output Voltage - V 0.5 0.4 0.3 0.2 0.1 0 0 10 20 30 40 50 60 IOL - Low-Level Output Current - mA

Figure 7

TERMINAL OUTPUT VOLTAGE vs

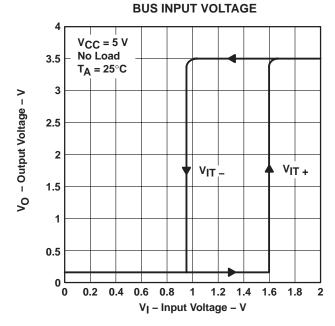


Figure 8

TYPICAL CHARACTERISTICS

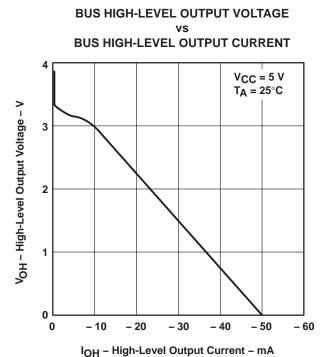
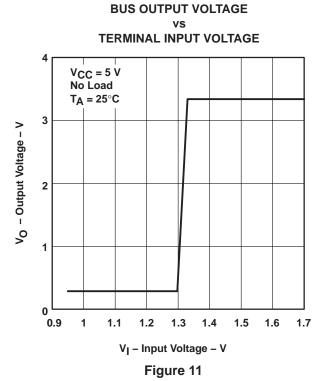
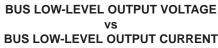


Figure 9





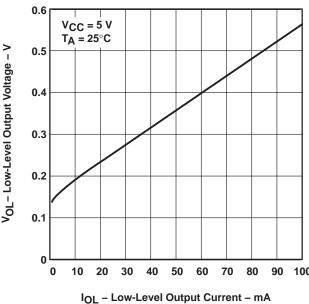
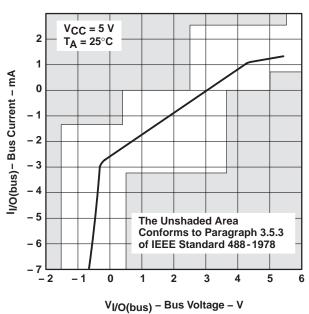


Figure 10

BUS CURRENT vs BUS VOLTAGE



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Figure 12



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN75ALS160DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS160	Samples
SN75ALS160DWE4	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS160	Samples
SN75ALS160DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	0 to 70	75ALS160	Samples
SN75ALS160DWRG4	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75ALS160	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN75ALS160:

• Military : SN55ALS160

NOTE: Qualified Version Definitions:

• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75ALS160DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75ALS160DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN75ALS160DWRG4	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1



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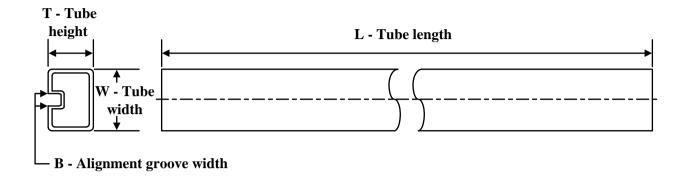
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN75ALS160DWR	SOIC	DW	20	2000	364.0	361.0	36.0
SN75ALS160DWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN75ALS160DWRG4	SOIC	DW	20	2000	367.0	367.0	45.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN75ALS160DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
SN75ALS160DW	DW	SOIC	20	25	507	12.83	5080	6.6
SN75ALS160DWE4	DW	SOIC	20	25	507	12.83	5080	6.6
SN75ALS160DWE4	DW	SOIC	20	25	506.98	12.7	4826	6.6



SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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